

# **N-Channel 150V MOSFET**

## E150N5P5GH1

V <sub>DS</sub> (V)	$R_{DS(on),max}$ (m $\Omega$ )	I <sub>D</sub> (A)
150V	5.8 @ V <sub>GS</sub> = 10V	205

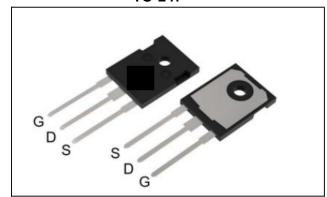
## **Features**

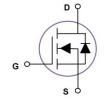
- Low R<sub>DS(on)</sub> trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

# **Applications**

- DC/DC conversion
- Power switch
- PD charger
- Moto driver

## TO-247







# **Package And Ordering Information**

Ordering code	Package	Marking
E150N5P5GH1	TO-247	E150N5P5GH1

**Ordering Information** 

Package	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box
TO-247	30	15	450



**Key Performance Parameters** 

Parameter	Value	Unit
VDS, min @ Tj(max)	150	V
ID, pulse	820	А
RDS(ON), max @ VGS=10V	5.8	mΩ
Qg	142	nC

Absolute Maximum Ratings at Tj=25°C Unless Otherwise Noted

Parameter		Symbol	Limit	Unit
Drain-source voltage		V <sub>DS</sub>	150	
Gate-source voltage		V <sub>GS</sub>	±25	V
	T <sub>C</sub> =25°C		205	
Continuous drain current	T <sub>C</sub> =100°C	- I <sub>D</sub>	145	
Pulsed drain current		I <sub>D,pulse</sub>	820	A
Avalanche energy, single pulse		E <sub>AS</sub>	1560	mJ
Dower discinction	T <sub>C</sub> =25°C		517	
Power dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	3.3	W
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C

## **Thermal Characteristics**

Parameter		Symbol	Max.	Uni t
Thermal resistance, junction-to-case	Steady state	R <sub>0</sub> JC	0.29	
Thermal resistance, junction-to-ambient	Steady state	Reja	38	°C/W

Electrical Characteristics at Tj=25°C unless otherwise specified

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
			Static			
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	150			V	V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA
Gate-source threshold voltage	V <sub>GS</sub> (th)	2.5	3	3.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA
Gate-body leakage	I <sub>GSS</sub>			±100	nA	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±25 V
Zero gate voltage drain current	I <sub>DSS</sub>			1	μA	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V
	D ()		4.8	5.8	mΩ	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 80 A
Drain-source on-resistance	R <sub>DS</sub> (on)		5.4	7.0	mΩ	V <sub>GS</sub> = 6 V, I <sub>D</sub> = 40 A
Forward transconductance	gfs		-		S	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 30 A



Gate resistance	Rg	0.5	2	4	Ω	f=1MHz
		Ga	te Char	ge		
Total gate charge	Qg		142	249		
Gate-source charge	Qgs		41	72	nC	V <sub>DS</sub> = 75 V, I <sub>D</sub> = 80 A, V <sub>GS</sub> = 10 V
Gate-drain charge	Qgd		32	56		
			ynamic	;		
Turn-on delay time	$t_{d(on)}$		31			
Rise time	tr		106			V <sub>DS</sub> = 75 V, I <sub>D</sub> =80 A, V <sub>GS</sub> = 10 V,
Turn-off delay time	$t_{\sf d(off)}$		96		ns	$R_{GEN}$ = 3.9 $\Omega$
Fall time	t <sub>f</sub>		109		113	
Input capacitance	C <sub>iss</sub>	4665	9325	16320		
Output capacitance	C <sub>oss</sub>	365	730	1275		V <sub>DS</sub> =75 V, V <sub>GS</sub> = 0 V, f = 100kHz
Reverse transfer capacitance	C <sub>rss</sub>	10	20	35	pF	
		Вс	dy Dio	de		
Diode forward voltage	$V_{\text{SD}}$		0.87	1	V	V <sub>GS</sub> = 0 V, I <sub>F</sub> = 80 A
Reverse recovery time	t <sub>rr</sub>		141	282	ns	V <sub>R</sub> = 75 V, I <sub>S</sub> =80 A, di/dt = 100
Reverse recovery charge	Qrr		499	998	nC	A/µs

# **Electrical Characteristics Diagrams**

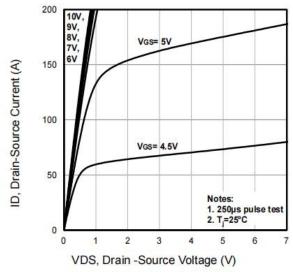


Fig1. Typical Output Characteristics

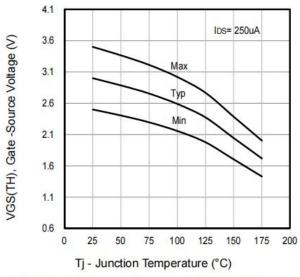


Fig2. Typical V<sub>GS(TH)</sub> Gate -Source Voltage Vs. Tj



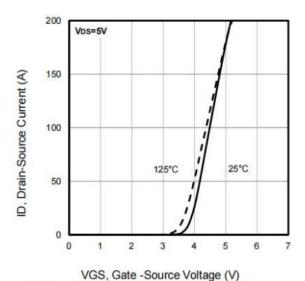


Fig3. Typical Transfer Characteristics

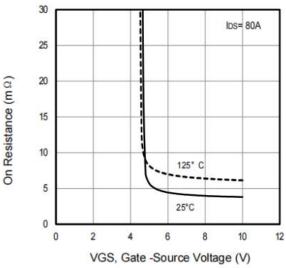


Fig5. Typical On Resistance Vs Gate -Source Voltage

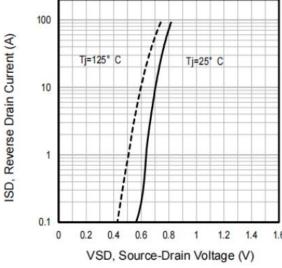
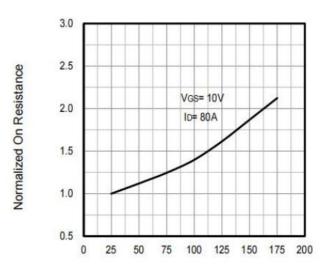


Fig7. Typical Source-Drain Diode Forward Voltage



Tj - Junction Temperature (°C)

Fig4. Typical Normalized On-Resistance Vs. Tj

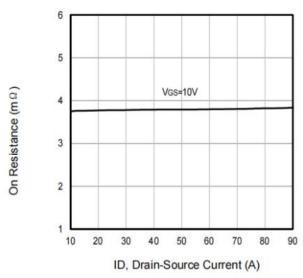


Fig6. Typical On Resistance Vs Drain Current

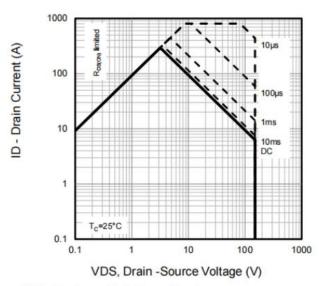


Fig8. Maximum Safe Operating Area

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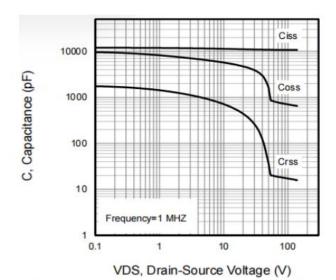


Fig9. Typical Capacitance Vs. Drain-Source Voltage

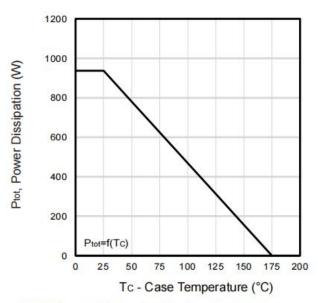


Fig11. Power Dissipation Vs. Case Temperature

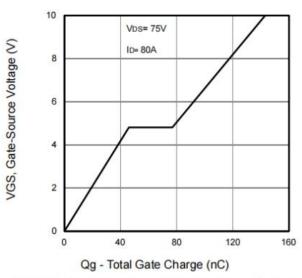


Fig10. Typical Gate Charge Vs. Gate-Source Voltage

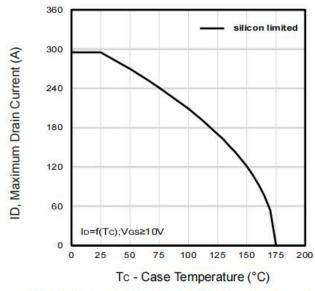


Fig12. Maximum Drain Current Vs. Case Temperature

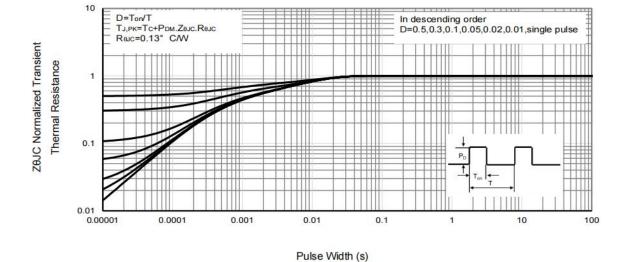


Fig13 . Normalized Maximum Transient Thermal Impedance

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## Test circuits and waveforms

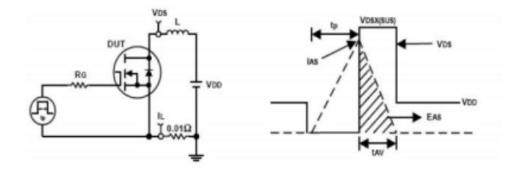


Fig14. Unclamped Inductive Test Circuit and waveforms

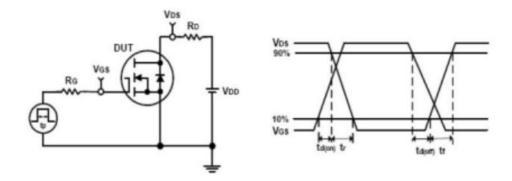
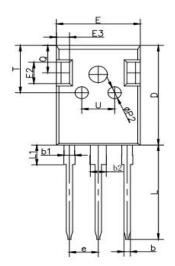
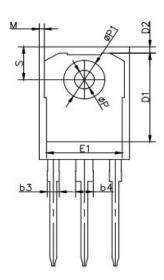


Fig15. Switching Time Test Circuit and waveforms



# **Package Outline Dimensions**





		47-3L	-	
DIM.	MIN.	NOM.	MAX.	
A	4.90	5.00	5.10	
A1	2.31	2.432	2.51	
A2	1.90	2.00	2.10	
ь	1.16	1.20	1.26	
b1	1.96	2.00	2.06	
b2	2.96	3.00	3.06	
b3	-	-	2.25	
b4		-	3.25	
c	0.59	0.60	0.66	
D	20.90	21.00	21.10	
D1	16.25	16.55	16.85	
D2	1.05	1.17	1.35	
E	15.70	15.80	15.90	
E1	13.10	13.26		
E2	4.40	4.50		
E3	2.40	2.50	2.60	
e		5.436BSC		
L	19.80	19.90	20.10	
L1	- 1-1	-	4.30	
М	0.35	0.89	0.95	
P	3.40	3.50	3.60	
P1	7.00	7.20	7.40	
P2	2.40	2.50	2.60	
Q	5.60	5.80	6.00	
S	6.05	6.15	6.25	
T	9.80	10.00	10.20	
U	6.00	6.20	6.40	



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